

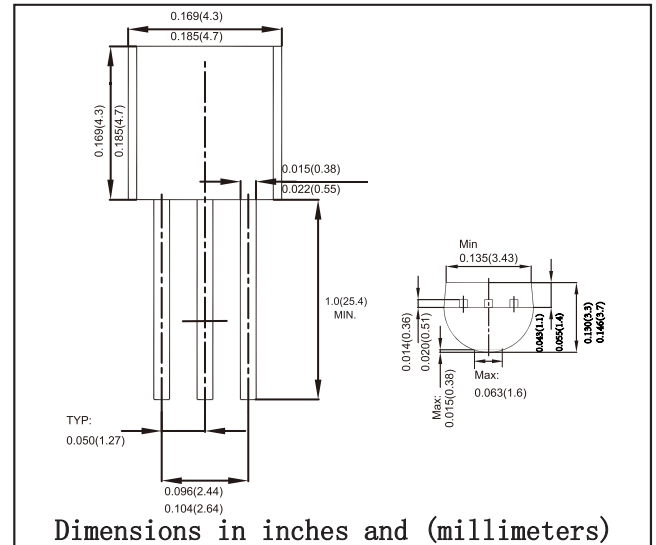
TO-92 Plastic-Encapsulate Transistors

FEATURES

- Low Frequency Amplifier
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	35	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current -Continuous	I_C	0.5	A
Collector Power Dissipation	P_C	400	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	312	°C /W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	- 50 ~ +150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 0.01mA, I_E = 0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	35			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.01mA, I_C = 0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB} = 20V, I_E = 0$			0.5	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3V, I_C = 0$			0.1	uA
DC current gain	$h_{FE(1)}$	$V_{CE} = 3V, I_C = 10mA$	60		320	
	$h_{FE(2)}$	$V_{CE} = 3V, I_C = 500mA$	10			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 150mA, I_B = 15mA$			0.6	V
Base-emitter voltage	V_{BE}	$V_{CE} = 3V, I_C = 10mA$			0.75	V

RATINGS AND CHARACTERISTIC CURVES

